MOSFETs Silicon N-channel MOS (U-MOSIX-H)

TPH1R005PL

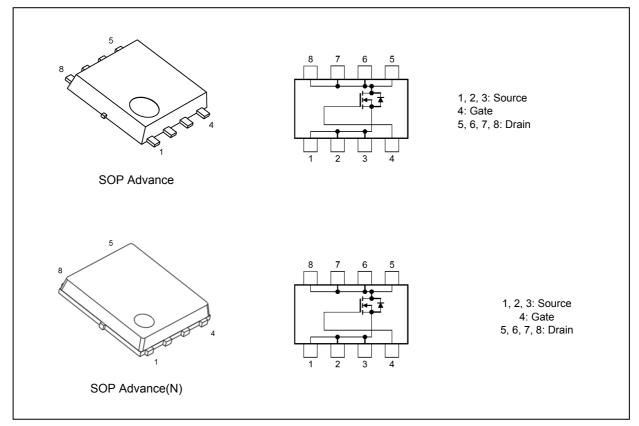
1. Applications

- High-Efficiency DC-DC Converters
- Switching Voltage Regulators

2. Features

- (1) High-speed switching
- (2) Small gate charge: $Q_{SW} = 34 \text{ nC}$ (typ.)
- (3) Small output charge: $Q_{oss} = 98 \text{ nC}$ (typ.)
- (4) Low drain-source on-resistance: $R_{DS(ON)} = 0.8 \text{ m}\Omega$ (typ.) ($V_{GS} = 10 \text{ V}$)
- (5) Low leakage current: I_{DSS} = 10 μ A (max) (V_{DS} = 45 V)
- (6) Enhancement mode: V_{th} = 1.4 to 2.4 V (V_{DS} = 10 V, I_D = 1.0 mA)

3. Packaging and Internal Circuit



The package can be selected according to your preference. For details, please contact your TOSHIBA sales representative.

4. Absolute Maximum Ratings (Note) (T_a = 25 °C unless otherwise specified)

Characterist	ics		Symbol	Rating	Unit
Drain-source voltage			V _{DSS}	45	V
Gate-source voltage			V _{GSS}	±20	
Drain current (DC)	(T _c = 25 °C)	(Note 1), (Note 2)	Ι _D	150	A
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	Ι _D	280	A
Drain current (pulsed)	(t = 100 μs)	(Note 1)	I _{DP}	500	A
Power dissipation	(T _c = 25 °C)		PD	170	×
Power dissipation		(Note 3)	PD	3.0	W
Power dissipation		(Note 4)	PD	0.96	W
Single-pulse avalanche energy		(Note 5)	E _{AS}	243	mJ
Single-pulse avalanche current		(Note 5)	I _{AS}	120	A
Channel temperature			T _{ch}	175	°C
Storage temperature			T _{stg}	-55 to 175	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit		
Channel-to-case thermal resistance	(T _c = 25 °C)		R _{th(ch-c)}	0.88	°C/W
Channel-to-ambient thermal resistance	(T _a = 25 °C)	(Note 3)	R _{th(ch-a)}	50	
Channel-to-ambient thermal resistance	(T _a = 25 °C)	(Note 4)	R _{th(ch-a)}	156	

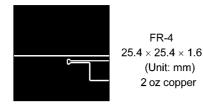
Note 1: Ensure that the channel temperature does not exceed 175 °C.

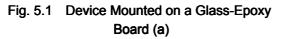
Note 2: Limited by package limit. Silicon chip capability is 280 A. ($T_c = 25 °C$)

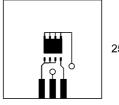
Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5: V_DD = 36 V, T_ch = 25 °C (initial), L = 13 $\mu H, \, I_{AS}$ = 120 A







FR-4 25.4 × 25.4 × 1.6 (Unit: mm) 2 oz copper

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V			±0.1	μA
Drain cut-off current	I _{DSS}	V _{DS} = 45 V, V _{GS} = 0 V			10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	45	_	—	V
	V _{(BR)DSX}	I _D = 10 mA, V _{GS} = -20 V	30	_	_	
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 1.0 mA	1.4	_	2.4	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 4.5 V, I _D = 50 A		1.2	1.7	mΩ
		V _{GS} = 10 V, I _D = 50 A		0.8	1.04	

6.2. Dynamic Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 22.5 V, V _{GS} = 0 V, f = 1 MHz	_	7700	9600	pF
Reverse transfer capacitance	C _{rss}		_	76	_	
Output capacitance	C _{oss}			1860	_	
Gate resistance	r _g	—	_	0.6	1.1	Ω
Switching time (rise time)	tr	See Fig. 6.2.1	_	17	_	ns
Switching time (turn-on time)	t _{on}			29	_	
Switching time (fall time)	t _f]		18	_	
Switching time (turn-off time)	t _{off}]		75	_	

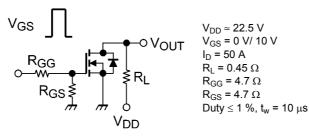


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25$ °C unless otherwise specified)

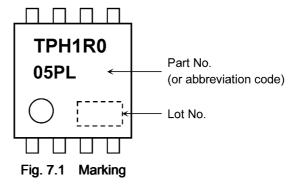
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus	Qg	$V_{DD}\approx 22.5$ V, V_{GS} = 10 V, I_{D} = 50 A	_	122	_	nC
gate-drain)		$V_{DD} \approx 22.5 \text{ V}, \text{ V}_{GS}$ = 4.5 V, I _D = 50 A	_	59	_	
Gate-source charge 1	Q _{gs1}	$V_{DD} \approx 22.5 \text{ V}, \text{ V}_{GS}$ = 10 V, I _D = 50 A	_	30	_	
Gate-drain charge	Q _{gd}		_	22	_	
Gate switch charge	Q _{SW}		—	34	_	
Output charge	Q _{oss}	V _{DS} = 22.5 V, V _{GS} = 0 V	_	98	_	

6.4. Source-Drain Characteristics ($T_a = 25$ °C unless otherwise specified)

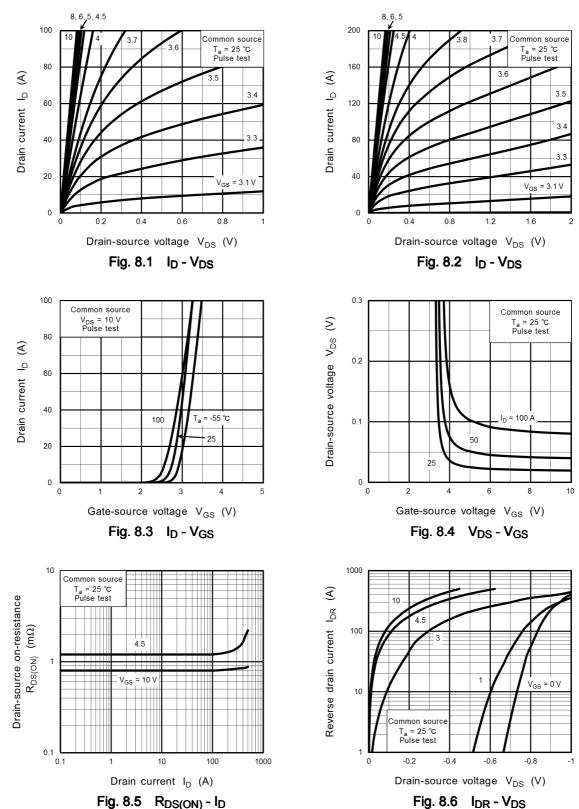
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (No	te 6) I _{DRP}	(t = 100 μs)	_	_	500	А
Diode forward voltage	V _{DSF}	I _{DR} = 150 A, V _{GS} = 0 V	_		-1.2	V
Reverse recovery time	t _{rr}	V_{R} = 22.5 V, I _{DR} = 37.5 A, V _{GS}	_	58	—	ns
Reverse recovery charge	Q _{rr}	= 0 V, -dl/dt = 100 A/μs		66	_	nC

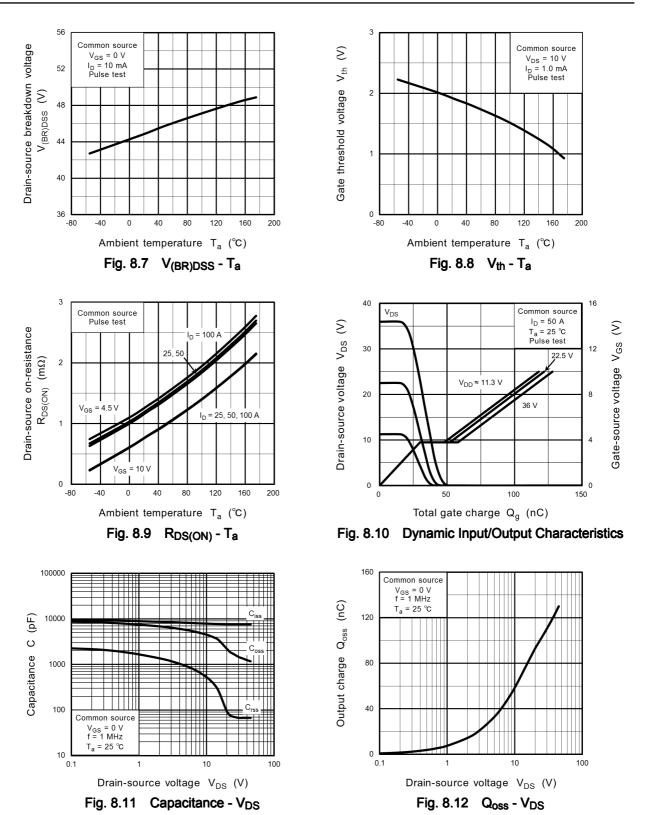
Note 6: Ensure that the channel temperature does not exceed 175 °C.

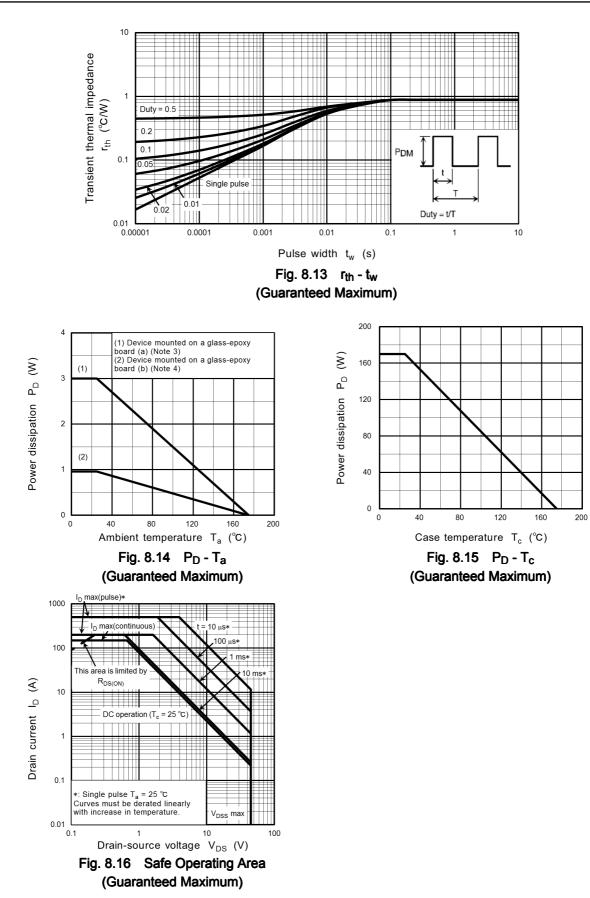
7. Marking



8. Characteristics Curves (Note)





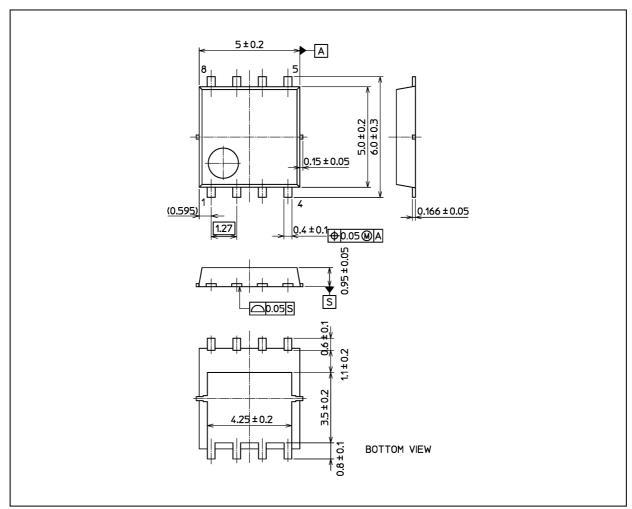


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

TPH1R005PL

Package Dimensions

Unit: mm



The package can be selected according to your preference. For details, please contact your TOSHIBA sales representative.

Weight: 0.087 g (typ.)

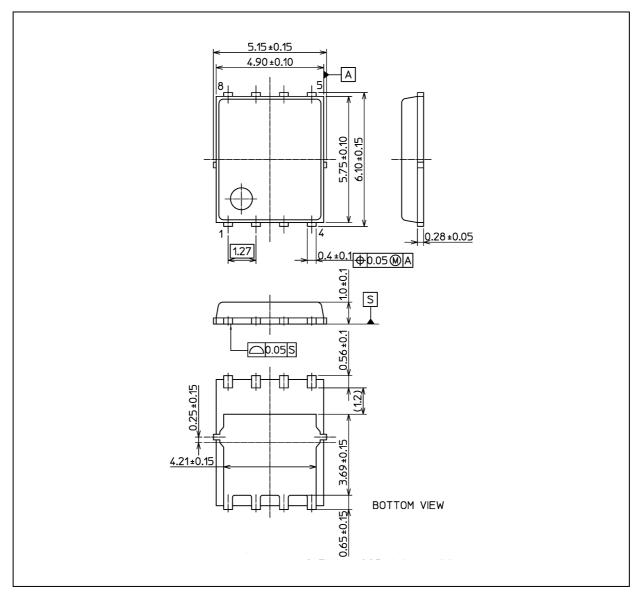
	Package Name(s)
TOSHIBA: 2-5Q1S	
Nickname: SOP Advance	



TPH1R005PL

Package Dimensions

Unit: mm



The package can be selected according to your preference. For details, please contact your TOSHIBA sales representative.

Weight: 0.111 g (typ.)

Package Name(s)
TOSHIBA: 2-5W1A
Nickname: SOP Advance(N)

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